



160V/140mA Switching Applications

Applications

· Predrivers for 100W power amplifiers.

Features

- · Adoption of FBET process.
- · Excellent linearity of hFE.
- · Small Cob.
- · Plastic-convered heat sink facilitating high-density mounting (TO-126ML package).

(): 2SA1477

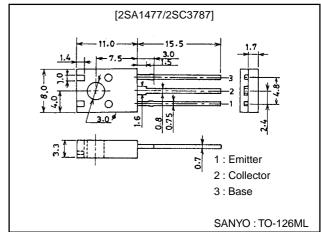
Specifications

Absolute Maximum Ratings at Ta = 25°C

Package Dimensions

unit:mm

2042B



Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CBO}		(–)180	V
Collector-to-Emitter Voltage	VCEO		(–)160	V
Emitter-to-Base Voltage	V _{EBO}		(–)5	V
Collector Current	IC		(–)140	mA
Peak Collector Current	I _{CP}		(–)200	mA
Collector Dissipation	PC		1.3	W
		Tc=25°C	10	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

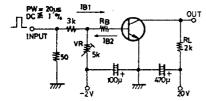
Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector Cutoff Current	ICBO	V _{CB} =(-)120V, I _E =0			(-)100	nA
Emitter Cutoff Current	I _{EBO}	V _{EB} =(-)4V, I _C =0			(-)100	nA
DC Current Gain	hFE	V _{CE} =(-)5V, I _C =(-)10mA	100		400	
Gain-Bandwidth Product	fT	V _{CE} =(-)10V, I _C =(-)10mA		150		MHz
Output Capacitance	C _{ob}	V _{CB} =(-)10V, f=1MHz		(4.0)		pF
				3.0		pF
Collector-to-Emitter Saturation Voltage	VCE(sat)	I _C =(-)50mA, I _B =(-)5mA		(-140)	(-400)	mV
				70	300	mV
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =(-)50mA, I _B =(-)5mA			1.2	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	I _C =(-)10μΑ, I _E =0	(-)180			V
Collector-to-Emitter Breakdown Voltage	V _(BR) CEO	I _C =(−)1mA, R _{BE} =∞	(-)160			V
Emitter-to-Base Breakdown Votage	V _{(BR)EBO}	I _E =(-)10μA, I _C =0	(–)5			V
Rise Time	ton	See specified Test Circuit		0.1		μs
Storage Time	t _{stg}	See specified Test Circuit		0.5		μs
Fall Time	t _f	See specified Test Circuit		0.1		μs

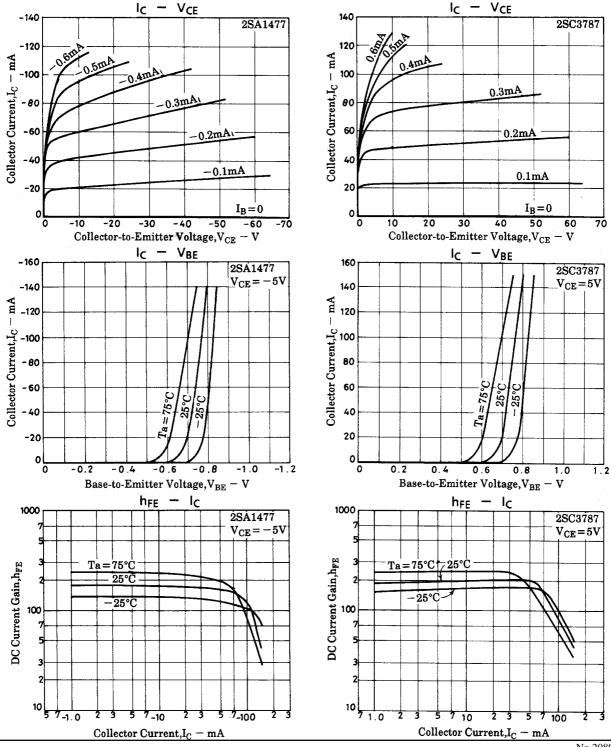
^{*:} The 2SA1477/2SC3787 are classified by 10mA $h_{\mbox{\scriptsize FE}}$ as follows :

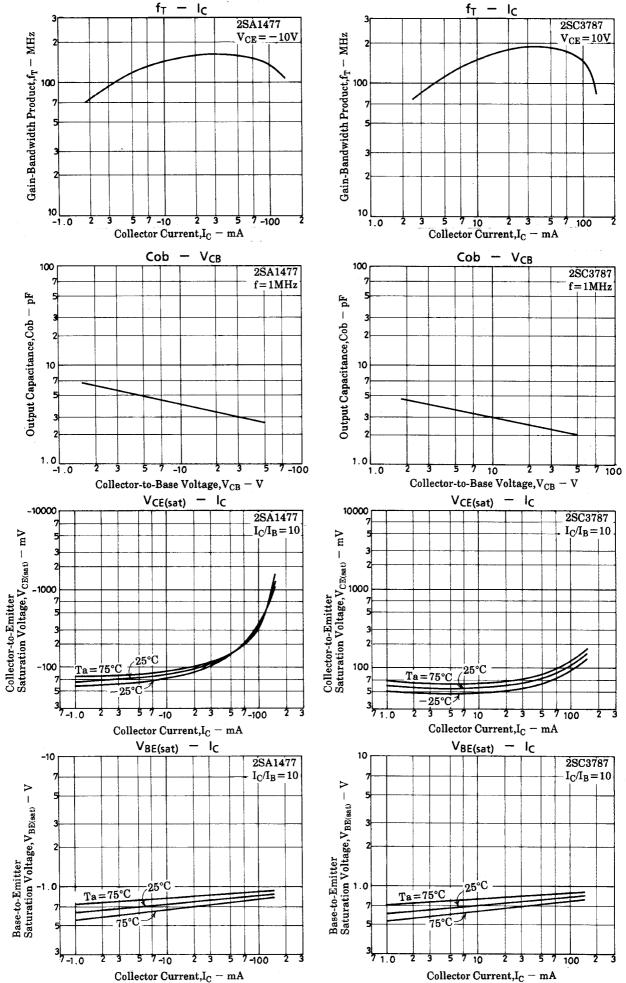
100 R 200 140 S 280 200 T 400

Switching Time Test Circuit

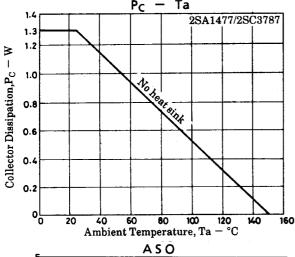


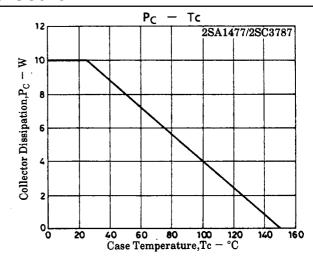
 $I_C = 10I_B1 = 10I_B2 = 10mA$ (For PNP, the polarity is reversed) Unit (resistance : Ω , capacitance : F)

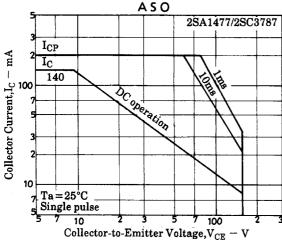




2SA1477/2SC3787







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